**AMENDMENTS TO THE CLAIMS:**

The following listing of claims replaces all prior versions and listings of claims in the application.

**Listing of Claims:**

Claim 1 (currently amended): A semiconductor light emitting device comprising:

an active layer composed of a nitride based semiconductor;

a cladding layer formed on said active layer, composed of a nitride based semiconductor of a first conductivity type, and having a flat portion and a ridge portion formed on the flat portion;

a first current blocking layer formed on said flat portion and on sidewalls of said ridge portion of said cladding layer and composed of a high-resistive nitride based semiconductor containing impurities; and

a second current blocking layer formed on said first current blocking layer and composed of a nitride based semiconductor of a second conductivity type opposite to said first conductivity type:

wherein the cladding layer is composed of AlGaN;

wherein the first current blocking layer is composed of AlGaN having a larger Al composition ratio than that of the cladding layer; ~~and~~

wherein said impurities contain at least one of zinc, beryllium, calcium, and carbon,

wherein said first current blocking layer has a resistance value of not less than 1.5 Ω·cm.

Claims 2-4 (canceled)

Claim 5 (original): The semiconductor light emitting device according to claim 1, wherein the thickness of said first current blocking layer is not less than 0.5 μm.

Claim 6 (original): The semiconductor light emitting device according to claim 5, wherein the thickness of said first current blocking layer is not less than 1.0 μm.

Claim 7 (original): The semiconductor light emitting device according to claim 1, wherein the thickness of the flat portion of said cladding layer is not more than 0.3 μm.

Claim 8 (previously presented): The semiconductor light emitting device according

to claim 7, wherein the thickness of the flat portion of said cladding layer is not more than 0.08 $\mu$m.

Claim 9 (original): The semiconductor light emitting device according to claim 1, wherein said nitride based semiconductor contains at least one of boron, gallium, aluminum, indium, and thallium.

Claim 10 (previously presented): The semiconductor light emitting device according to claim 1, wherein

said cladding layer having a recess on said flat portion along both sidewalls of said ridge portion; and

said first current blocking layer is formed on said flat portion and on the sidewalls of said ridge portion such that it is embedded in said recess of said cladding layer.

Claims 11-19 (canceled)